

FDS6064N3

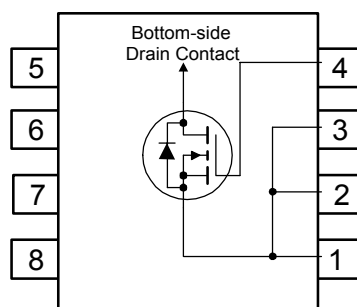
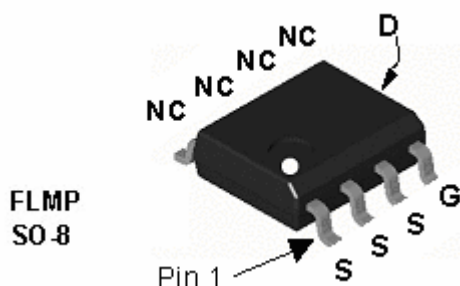
20V N-Channel PowerTrench® MOSFET

General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for "low side" synchronous rectifier operation, providing an extremely low $R_{DS(ON)}$ in a small package.

Applications

- Synchronous rectifier
- DC/DC converter
- FLMP SO-8 package: Enhanced thermal performance in industry-standard package size



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	20	V
V _{GSS}	Gate-Source Voltage	± 8	
I _D	Drain Current – Continuous (Note 1a)	23	A
	– Pulsed	60	
P _D	Power Dissipation (Note 1a)	3.0	W
T _J , T _{STG}	Operating and Storage Junction Temperature Range	–55 to +150	°C

Thermal Characteristics

R _{θJA}	Thermal Resistance, Junction-to-Ambient (Note 1a)	40	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	0.5	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6064N3	FDS6064N3	13"	12mm	2500 units

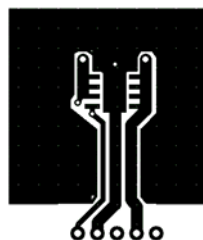
Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		11		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$			1	μA
I_{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.4	0.6	1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C		-3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 4.5\text{ V}, I_D = 23\text{ A}$ $V_{GS} = 2.5\text{ V}, I_D = 22\text{ A}$ $V_{GS} = 1.8\text{ V}, I_D = 18\text{ A}$ $V_{GS} = 4.5\text{ V}, I_D = 23\text{ A}, T_J = 125^\circ\text{C}$		3.4 3.8 4.9 4.5	4 5 7 8	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 23\text{ A}$		179		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}$		7191		pF
C_{oss}	Output Capacitance	$f = 1.0\text{ MHz}$		1403		pF
C_{rss}	Reverse Transfer Capacitance			703		pF
R_G	Gate Resistance	$V_{GS} = 15\text{ mV}, f = 1.0\text{ MHz}$		1.2		Ω
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 10\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 4.5\text{ V}, R_{GEN} = 6\ \Omega$		22	35	ns
t_r	Turn–On Rise Time			22	35	ns
$t_{d(off)}$	Turn–Off Delay Time			153	245	ns
t_f	Turn–Off Fall Time			77	123	ns
Q_g	Total Gate Charge	$V_{DS} = 10\text{ V}, I_D = 23\text{ A},$ $V_{GS} = 4.5\text{ V}$		70	98	nC
Q_{gs}	Gate–Source Charge			10		nC
Q_{gd}	Gate–Drain Charge			15		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				2.5	A
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 2.5\text{ A}$ (Note 2)		0.6	1.2	V
t_{rr}	Diode Reverse Recovery Time	$I_F = 23\text{ A},$ $dI_F/dt = 100\text{ A}/\mu\text{s}$		43		nS
Q_{rr}	Diode Reverse Recovery Charge			55		nC

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 40 $^\circ\text{C}/\text{W}$ when mounted on a 1in² pad of 2 oz copper



b) 85 $^\circ\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

Typical Characteristics

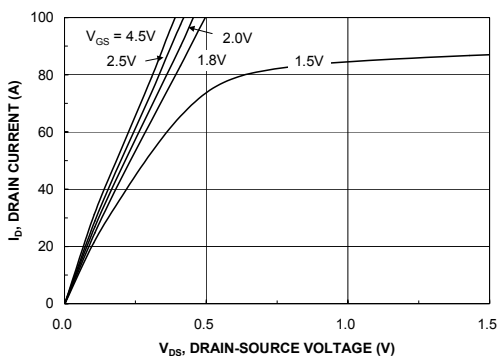


Figure 1. On-Region Characteristics.

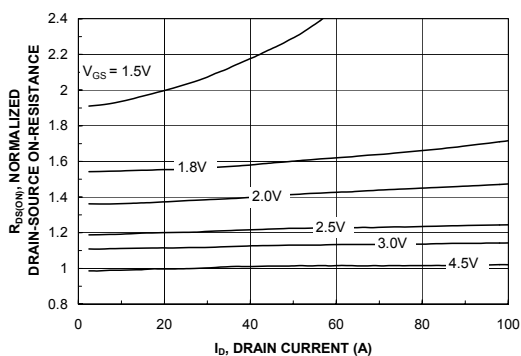


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

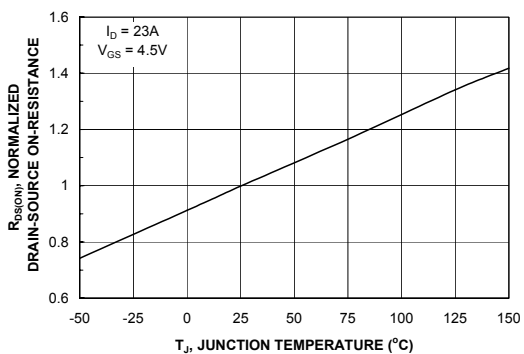


Figure 3. On-Resistance Variation with Temperature.

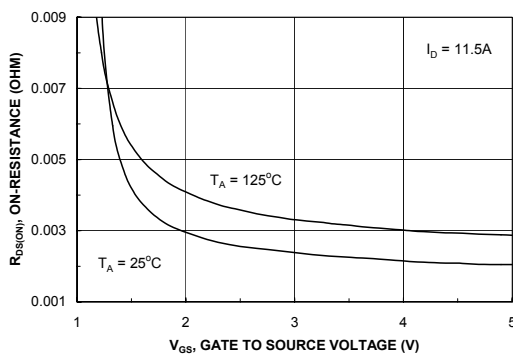


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

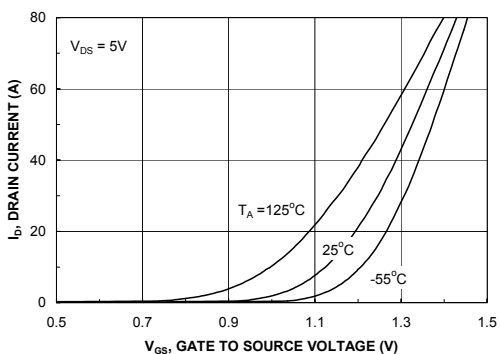


Figure 5. Transfer Characteristics.

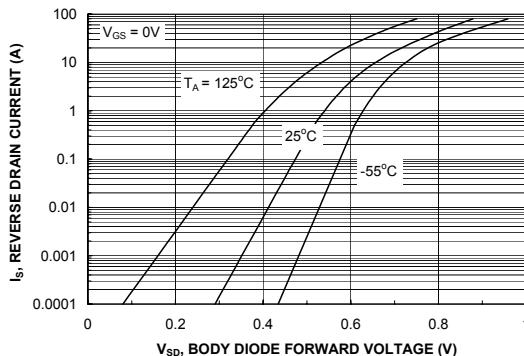


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics

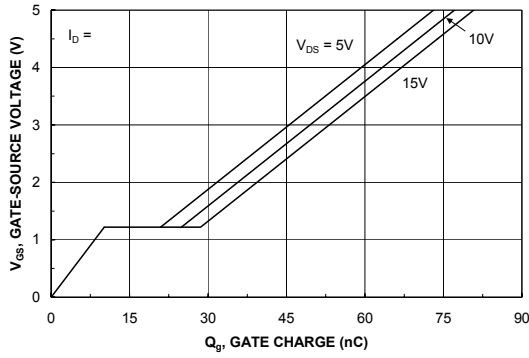


Figure 7. Gate Charge Characteristics.

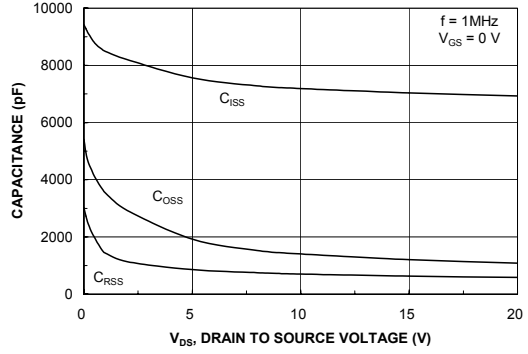


Figure 8. Capacitance Characteristics.

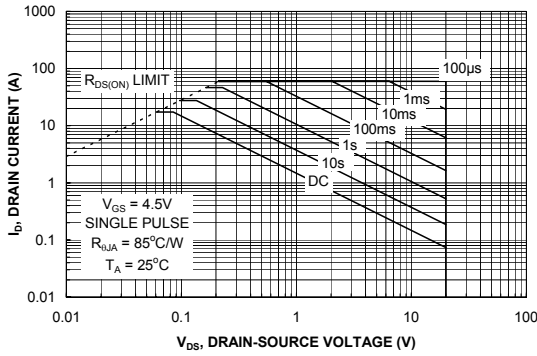


Figure 9. Maximum Safe Operating Area.

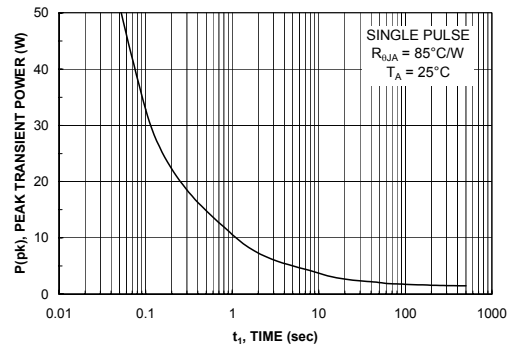


Figure 10. Single Pulse Maximum Power Dissipation.

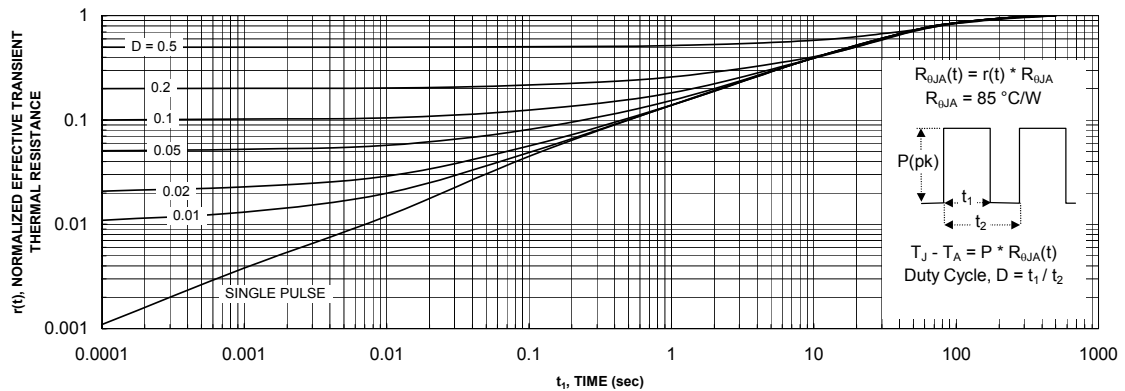
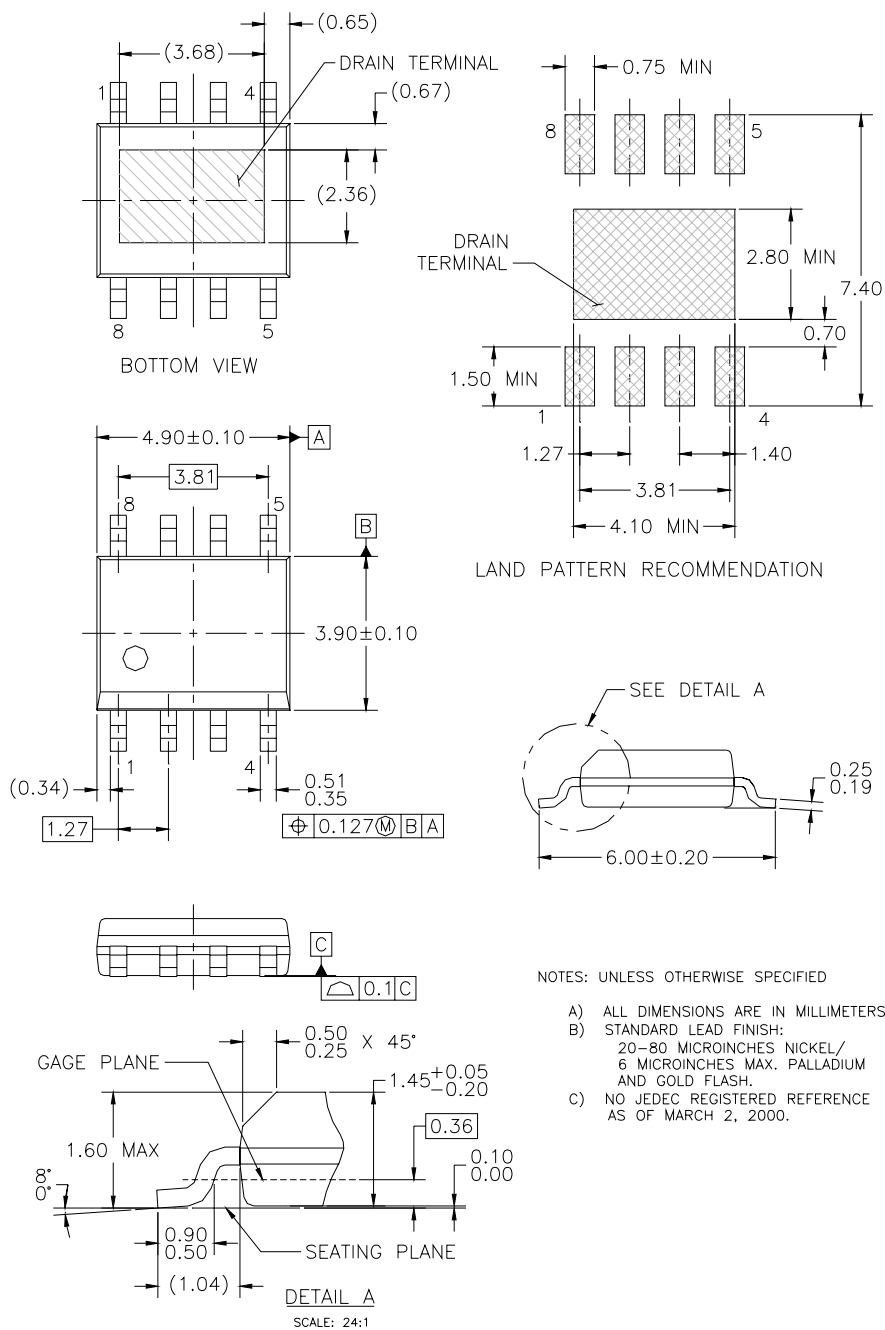


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

Dimensional Outline and Pad Layout



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